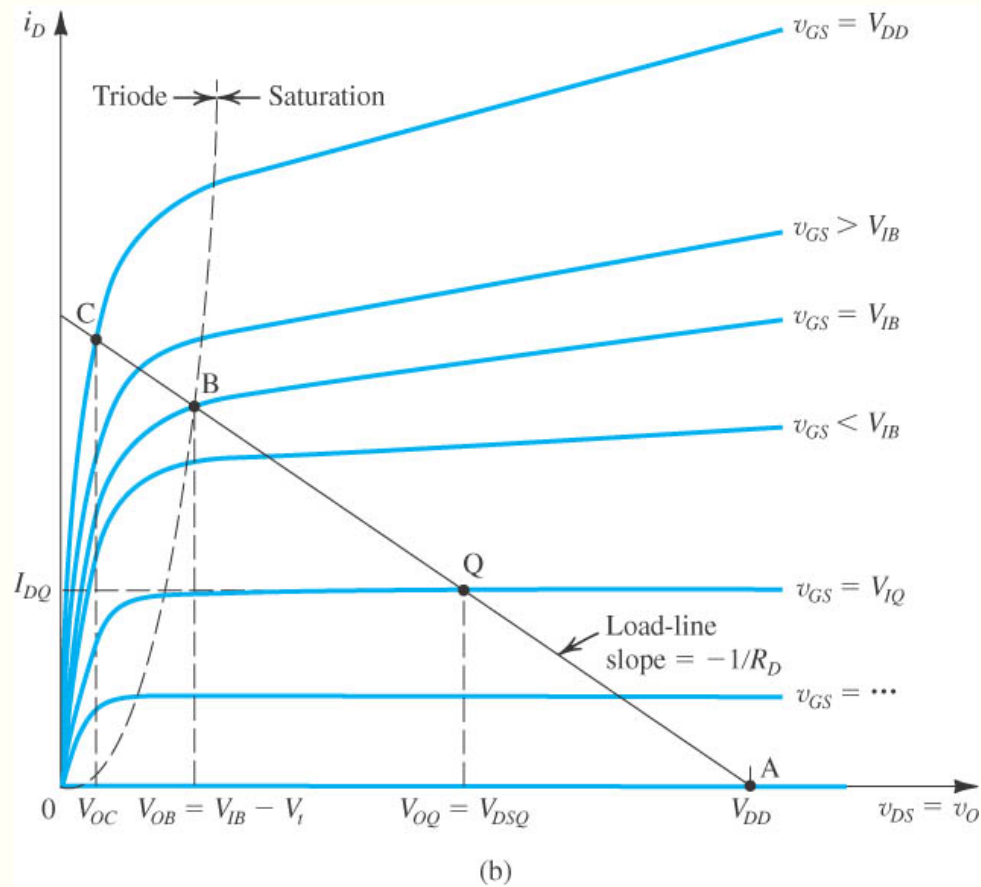
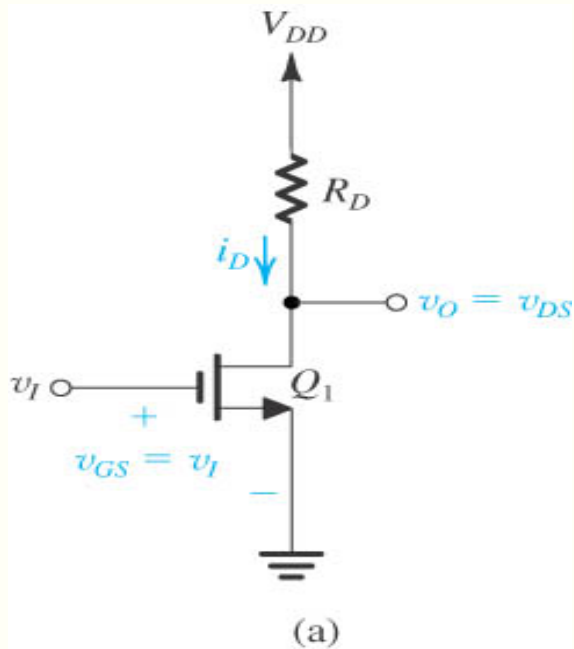
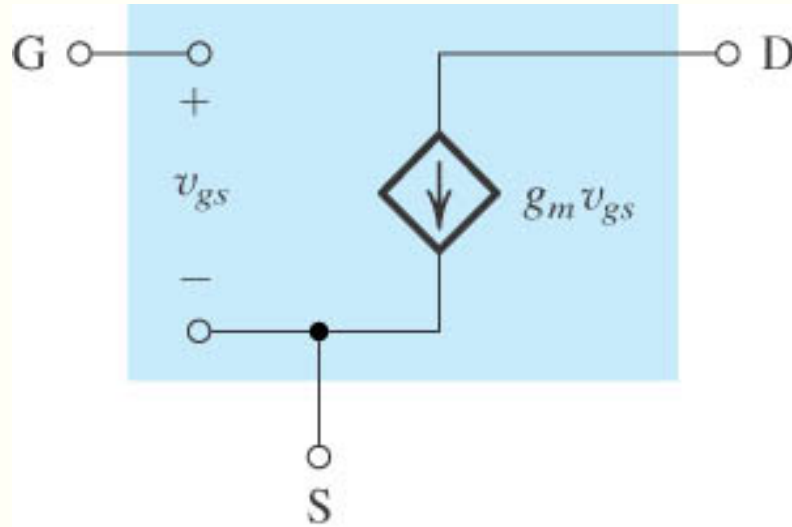


The MOSFET as an Amplifier

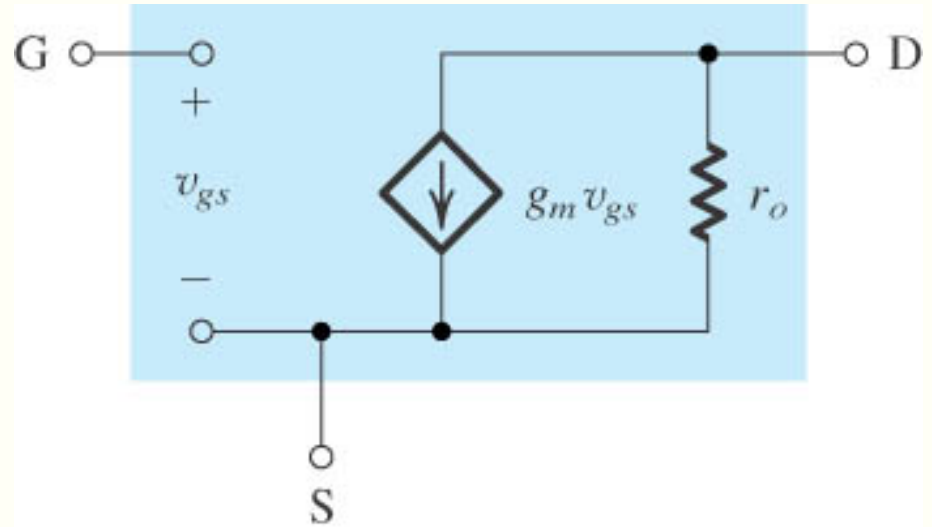


➤ Basic structure of the common-source amplifier.

The Small-Signal Models

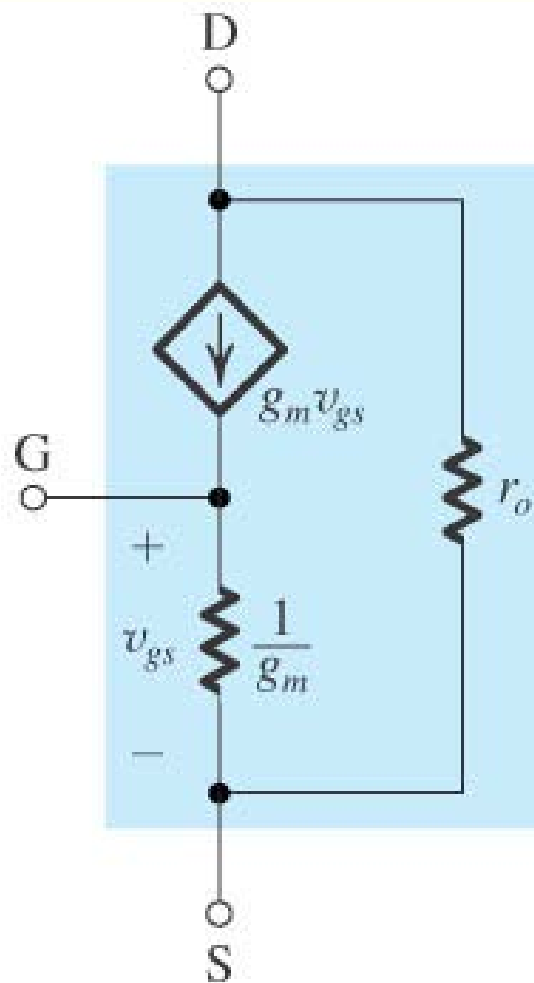
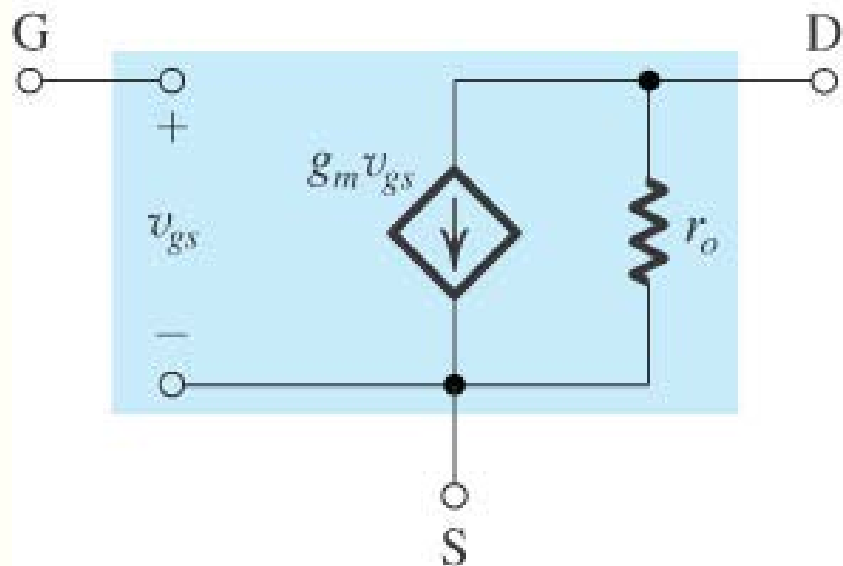


(a)



(b)

- (a) neglecting the the channel-length modulation effect
- (b) including the effect of channel-length modulation, modeled by output resistance $r_o = |V_A| / I_D$.



The ac Characteristics

Transconductance $g_m \equiv \left. \frac{\partial i_D}{\partial v_{GS}} \right|_{v_{GS}=V_{GS}} = k_n' \frac{W}{L} (V_{GS} - V_T)$

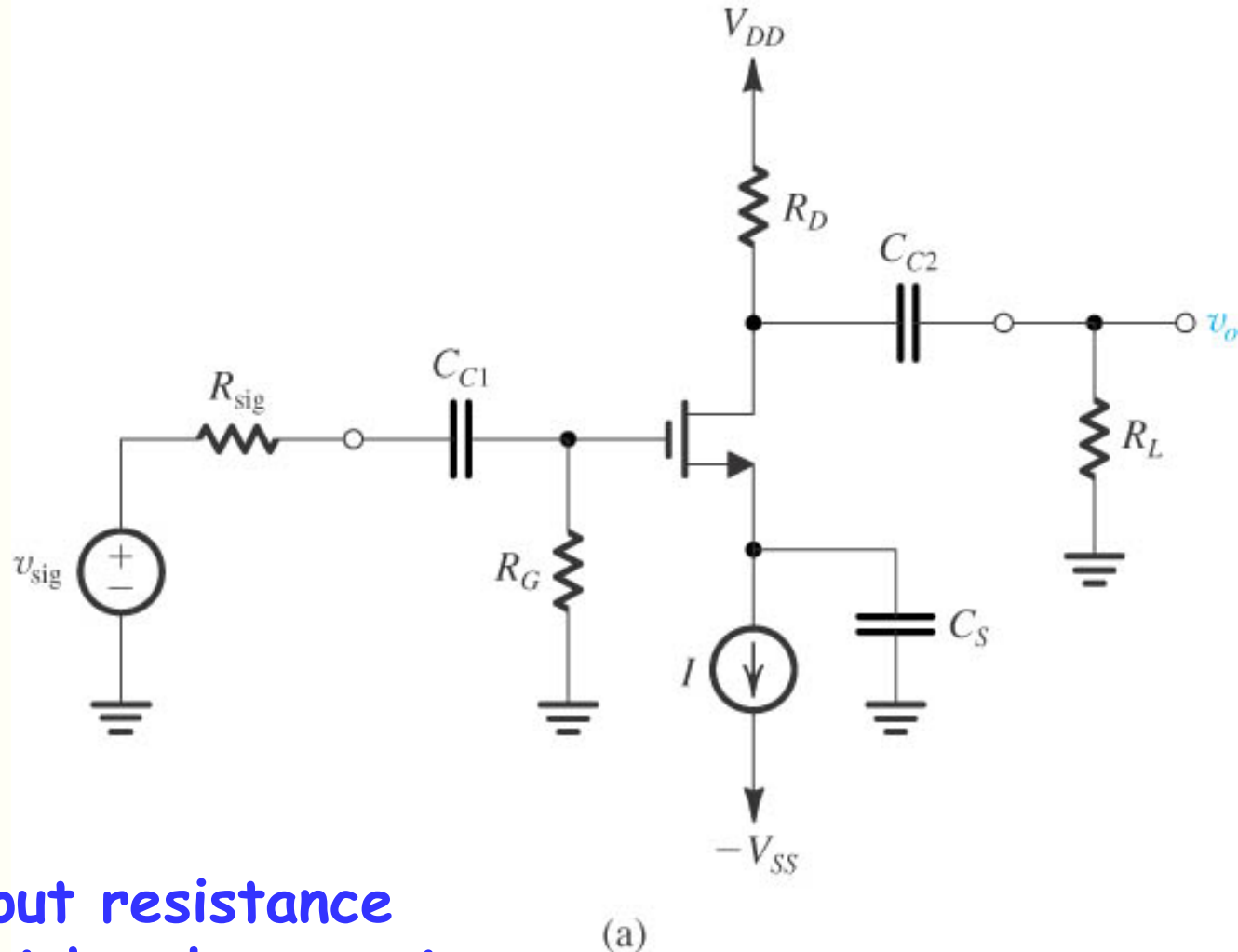
Output Resistance $r_o \equiv \left. \frac{\partial v_{DS}}{\partial i_D} \right|_{i_D=I_D} = \frac{V_A}{I_D}$

V_A is MOSFET parameter used to determine r_o

Voltage gain

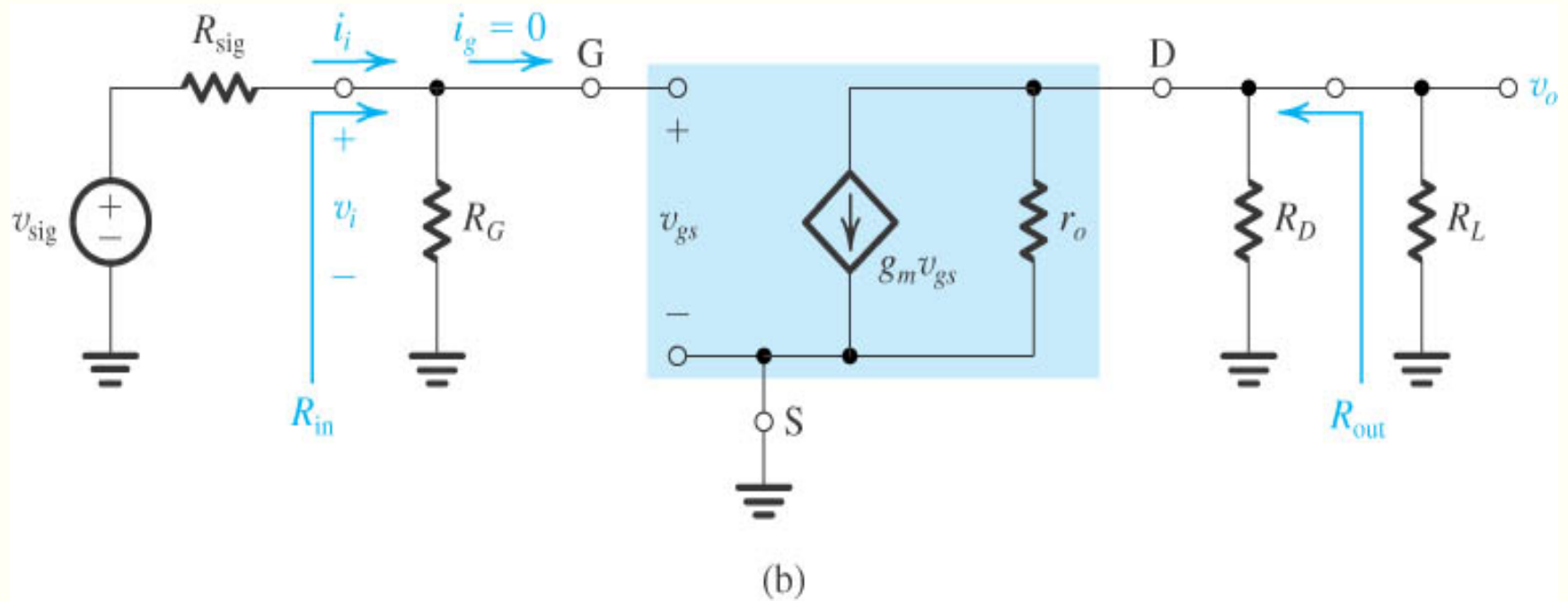
$$A_v \equiv \frac{v_o}{v_i}$$

The Common-Source Amplifier

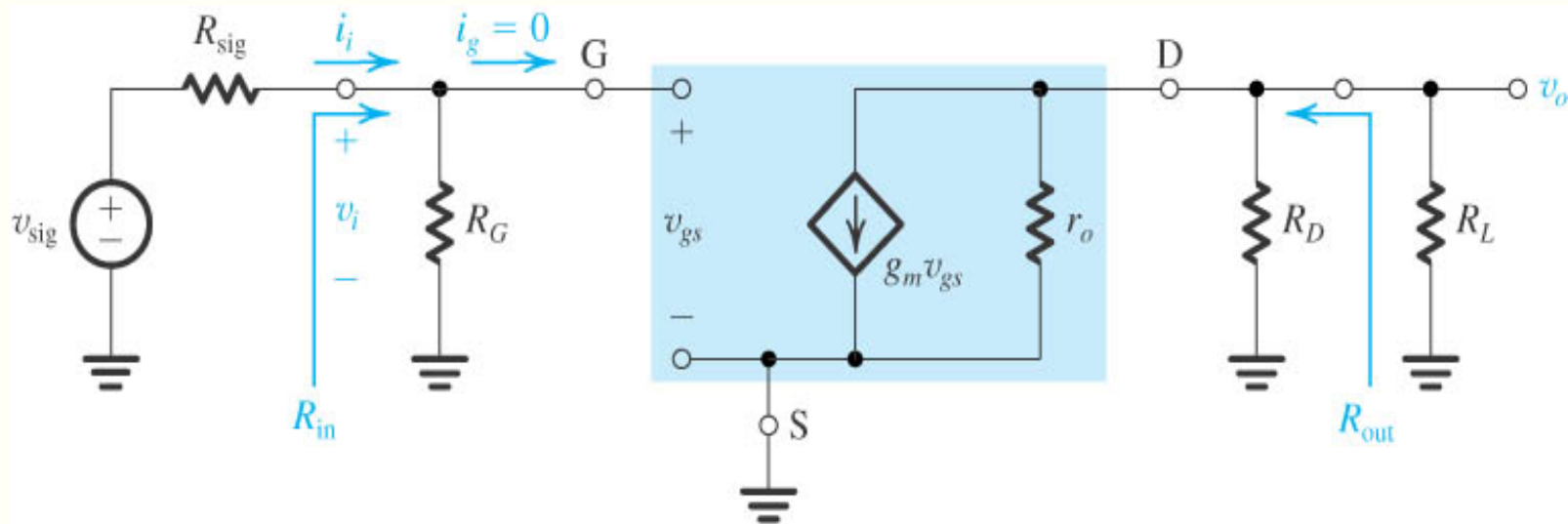


- Very high input resistance
- Moderately high voltage gain
- Relatively high output resistance

Equivalent Circuit of the CS Amplifier



Characteristics of CS Amplifier



Input resistance

$$R_{in} = R_G \quad (b)$$

Voltage gain

$$A_v = \frac{v_o}{v_{gs}} = -g_m (r_o // R_D // R_L)$$

Overall voltage gain

$$G_v = \frac{v_o}{v_{sig}} = -\frac{R_G}{R_G + R_{sig}} g_m (R_D // R_L // r_o)$$

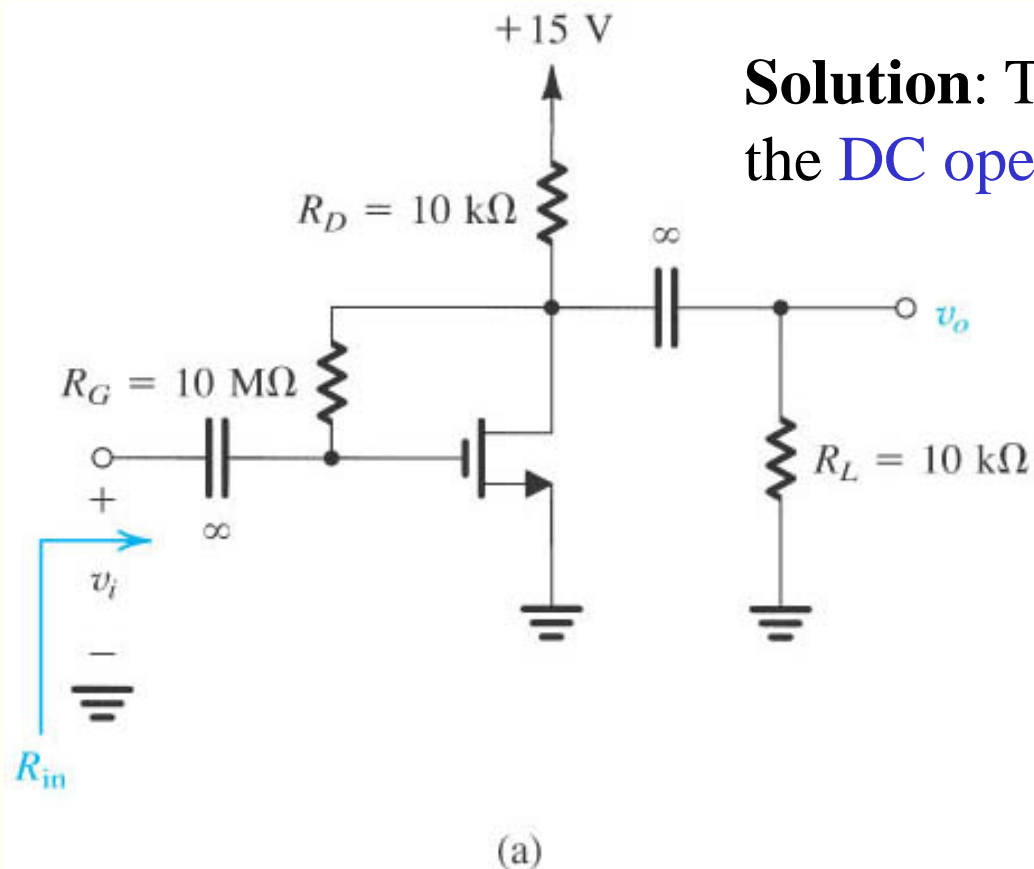
Output resistance

$$R_{out} = r_o // R_D$$

Example-9: Small signal analysis of MOSFET Amplifiers

Determine A_v (neglecting the effects of R_G), R_{in} , and R_{out} for the circuit shown in Fig.. given that $V_t = 1.5$ V, $V_A = 50$ V and

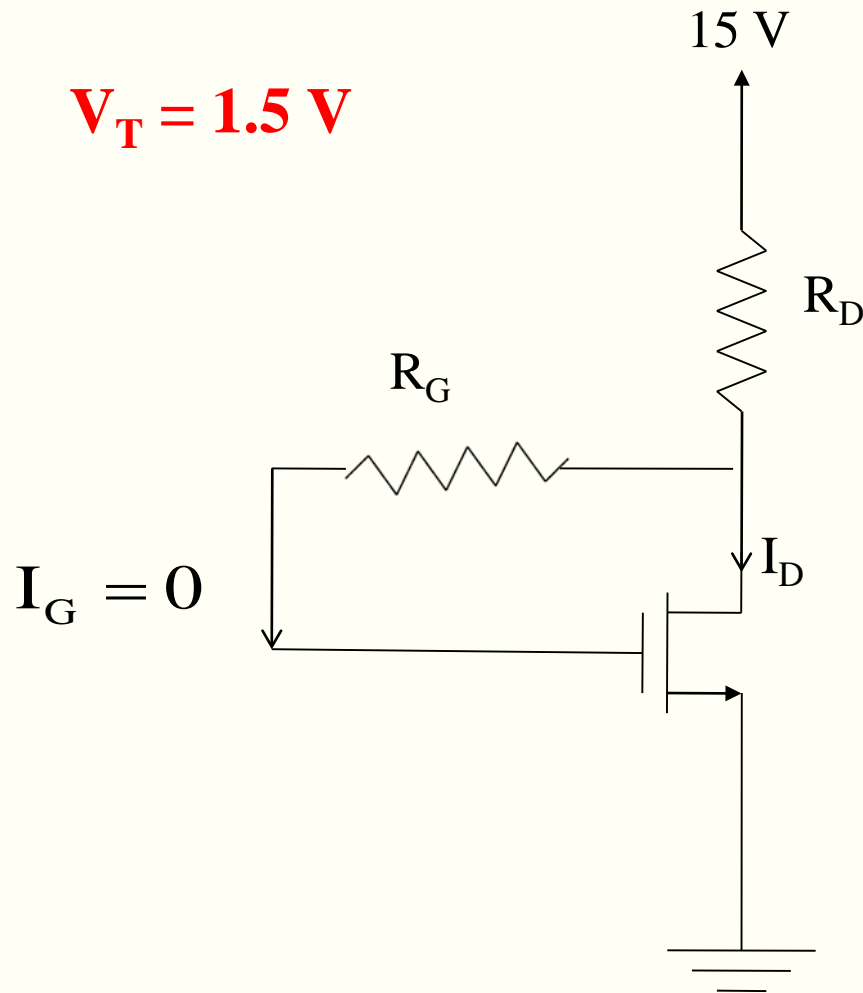
$$k'_n W/L = 0.25 \text{ mA/V}^2$$



Solution: The first step is to determine the **DC operating point**.

The DC equivalent circuit:

$$V_T = 1.5 \text{ V}$$



$$v_{GS} > V_T$$

$$v_{DS} > v_{GS} - V_T$$

Since $I_G = 0$, $V_G = V_D$

$$V_T > (v_{GS} - v_{DS})$$

$$V_T > 0$$

$$I_D = \frac{1}{2} \cdot 0.25 \times 10^{-3} (V_{GS} - 1.5)^2 = 1.25 \times 10^{-4} (V_{GS} - 1.5)^2$$

Since, $V_{GS} = V_{DS}$ $I_D = 0.125(V_{DS} - 1.5)^2 \text{ mA}$

$$V_{DS} = 15 - R_D I_D = 15 - 10 I_D$$

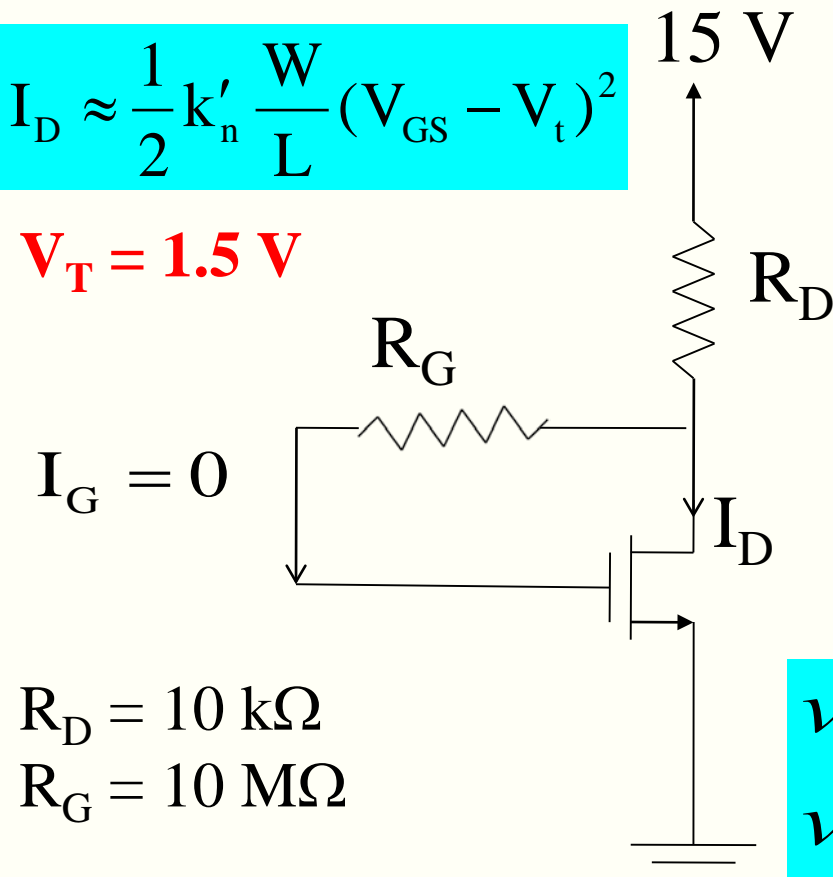
$$I_D = 0.125(15 - 10 I_D - 1.5)^2$$

$$I_D = 1.06 \text{ mA}$$

$$\Rightarrow V_{DS} = 4.4 \text{ V } (= V_{GS})$$

$$I_D = 1.72 \text{ mA}$$

$$\Rightarrow V_{DS} = -2.2 \text{ V } (= V_{GS})$$



$$v_{GS} > V_T$$

$$v_{DS} > v_{GS} - V_T$$

MOSFET is in saturation

For small signal analysis:

Transconductance

$$g_m = k'_n \frac{W}{L} (V_{GS} - V_t)$$

$$g_m = 0.25 \times 10^{-3} (4.4 - 1.5) = 0.725 \text{ mS}$$

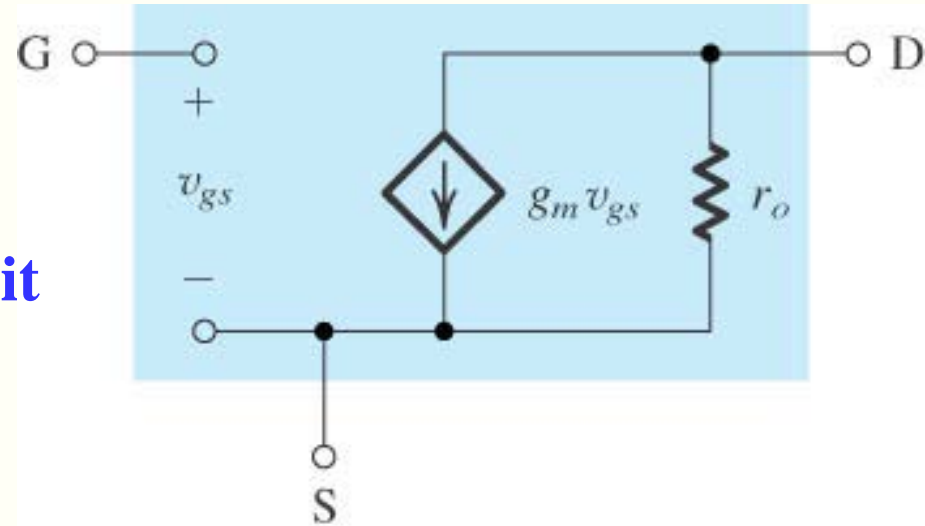
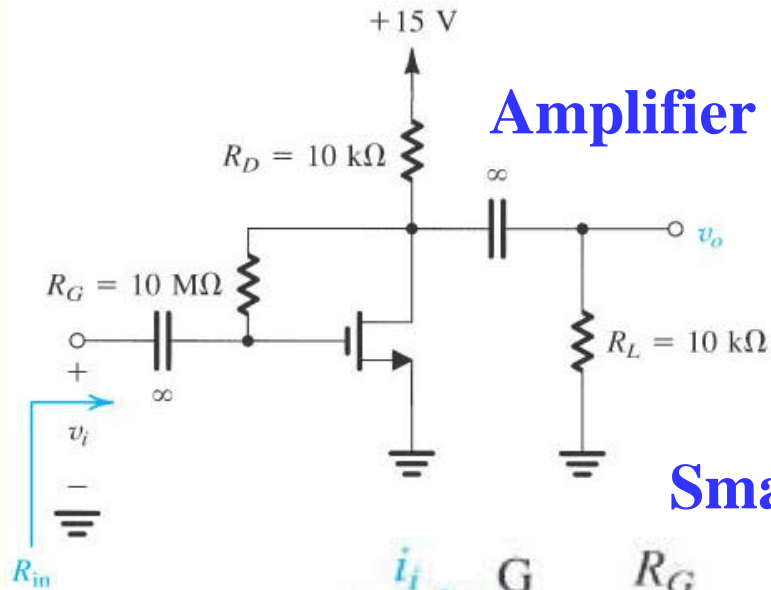
Output Resistance

$$r_0 = \frac{V_A}{I_D}$$

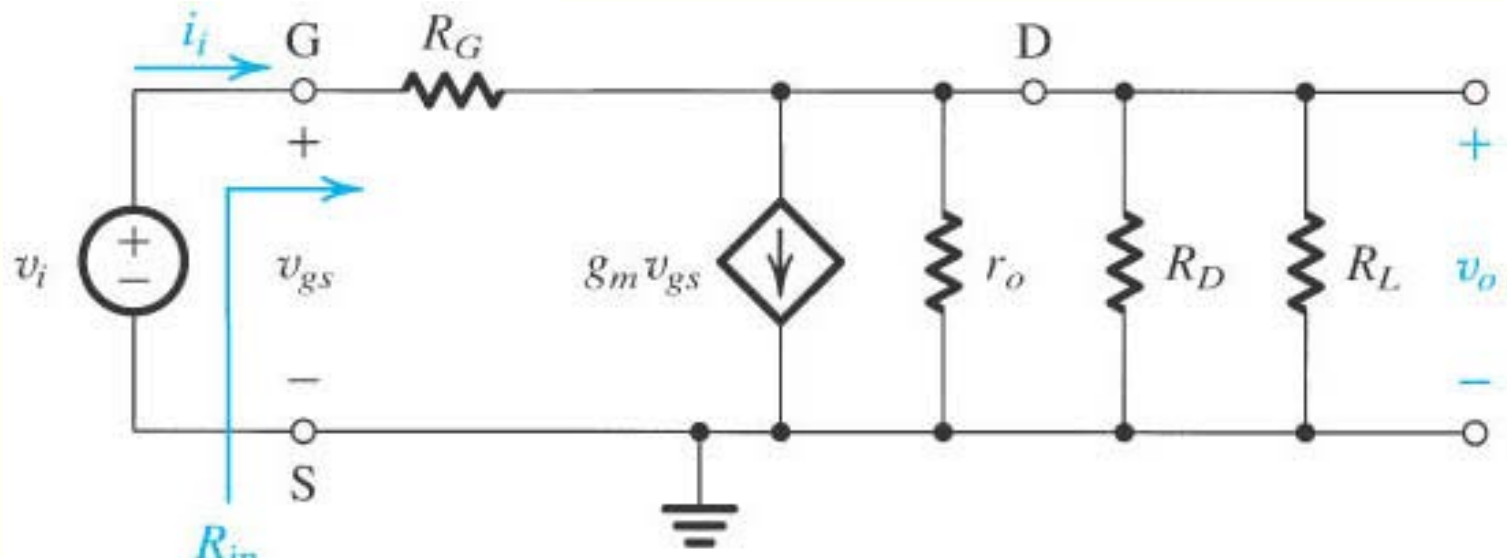
$$r_0 = \frac{V_A}{I_D} = \frac{50}{1.06 \text{ mA}} = 47.2 \text{ k}\Omega$$

For small signal analysis:

Amplifier Circuit



Small signal Equivalent circuit model



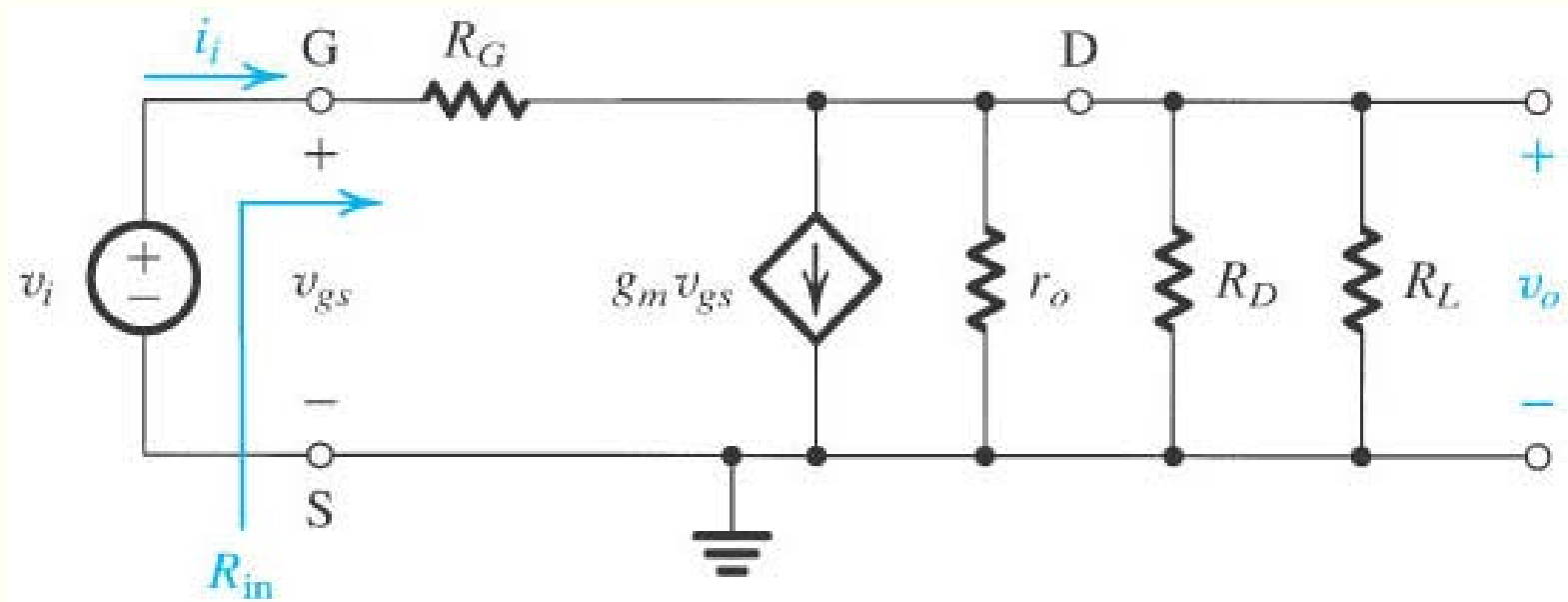
For small-signal voltage gain,

R_G is extremely large $R_G \gg r_o \parallel R_D \parallel R_L$

$$v_o \approx -g_m v_{gs} (r_o \parallel R_D \parallel R_L)$$

$$v_{gs} = v_i$$

$$A_v = \frac{v_o}{v_i} \approx -g_m (r_o \parallel R_D \parallel R_L) = -3.3$$



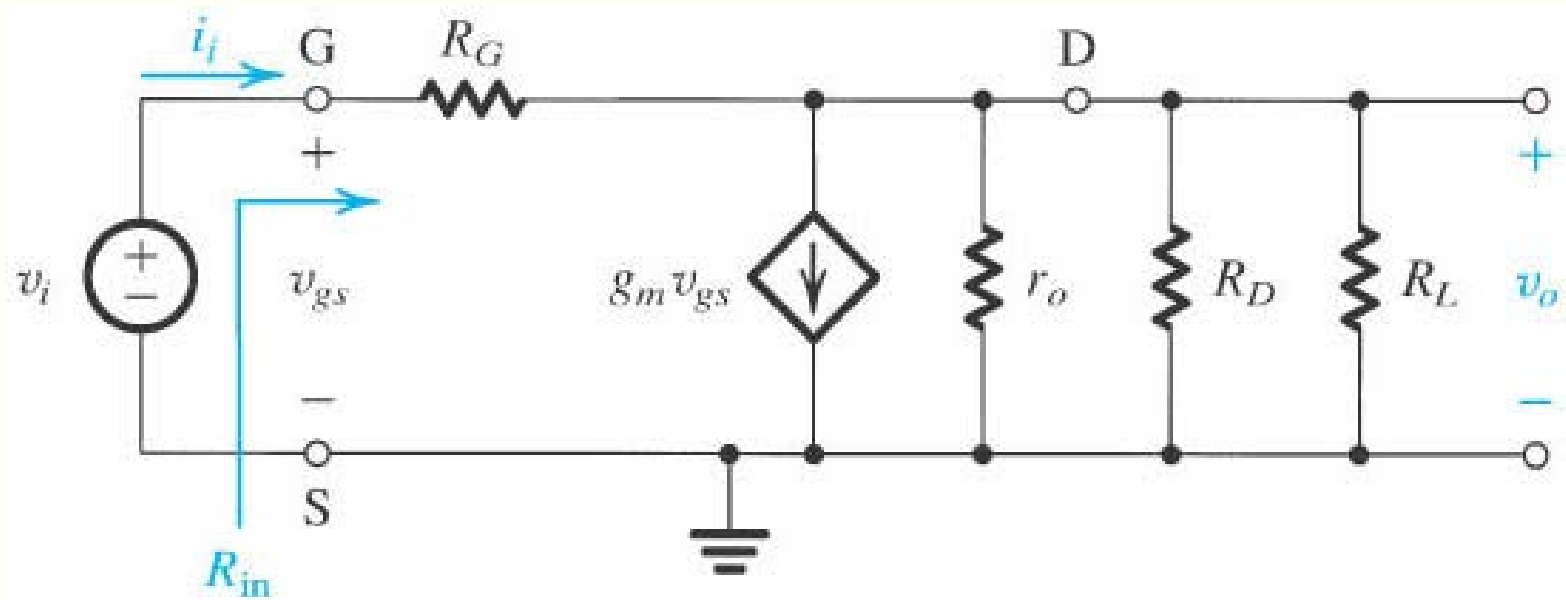
Input resistance

$$R_{in} \equiv \frac{v_i}{i_i}$$

$$i_i = \frac{v_i - v_o}{R_G} = \frac{v_i}{R_G} \left(1 - \frac{v_o}{v_i} \right) = \frac{v_i}{R_G} (1 - A_v)$$

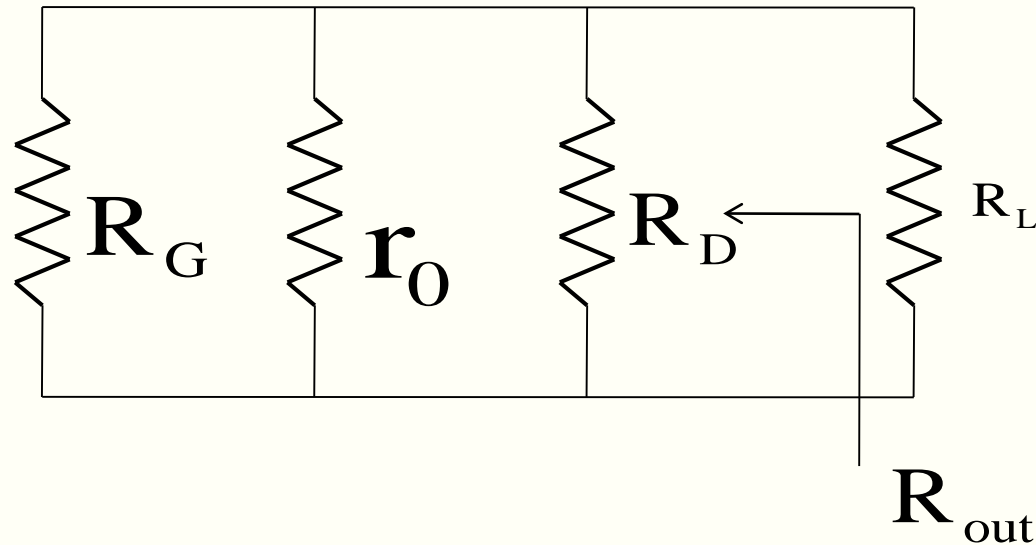
$$i_i = \frac{v_i}{R_G} (1 + 3.28)$$

$$R_{in} = \frac{v_i}{i_i} = \frac{R_G}{4.28} = 2.34 \text{ M}\Omega$$



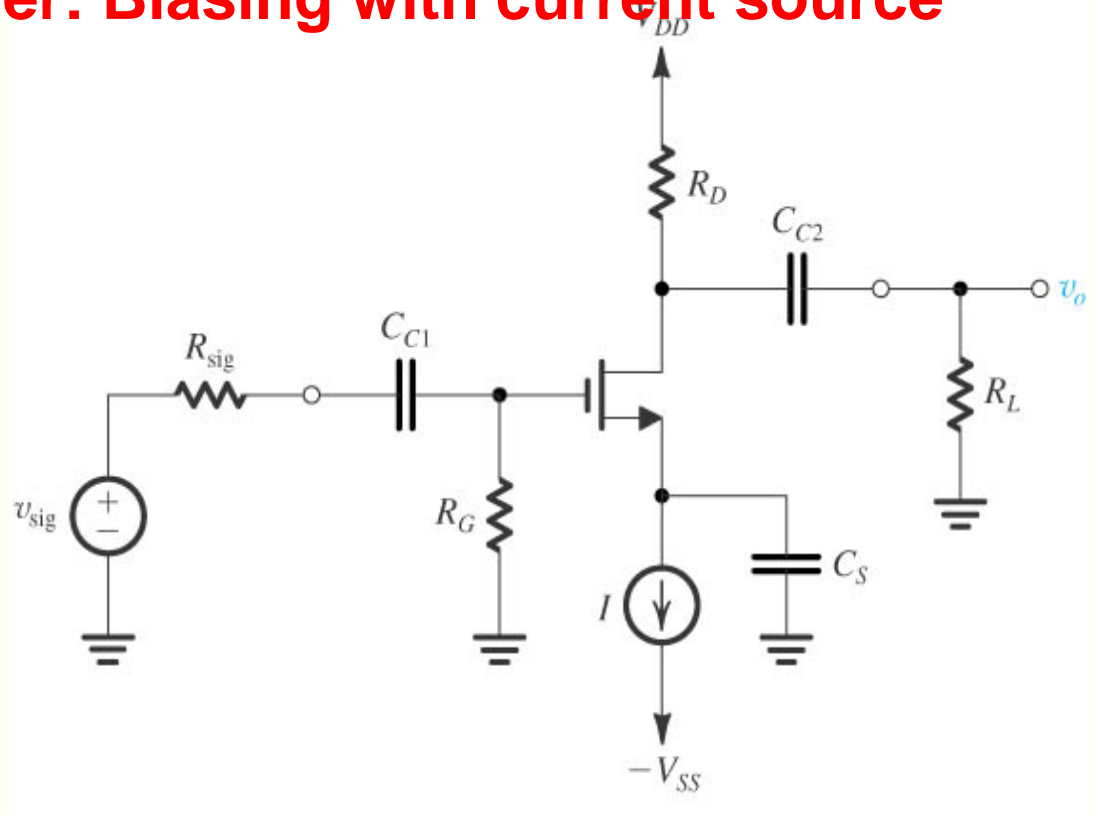
Output Resistance,

- To compute this we set $v_{gs} = 0$ in the small scale equivalent circuit, which will open circuit the dependent current source leading to equivalent circuit as shown below.
- From the figure we can compute R_{out} as



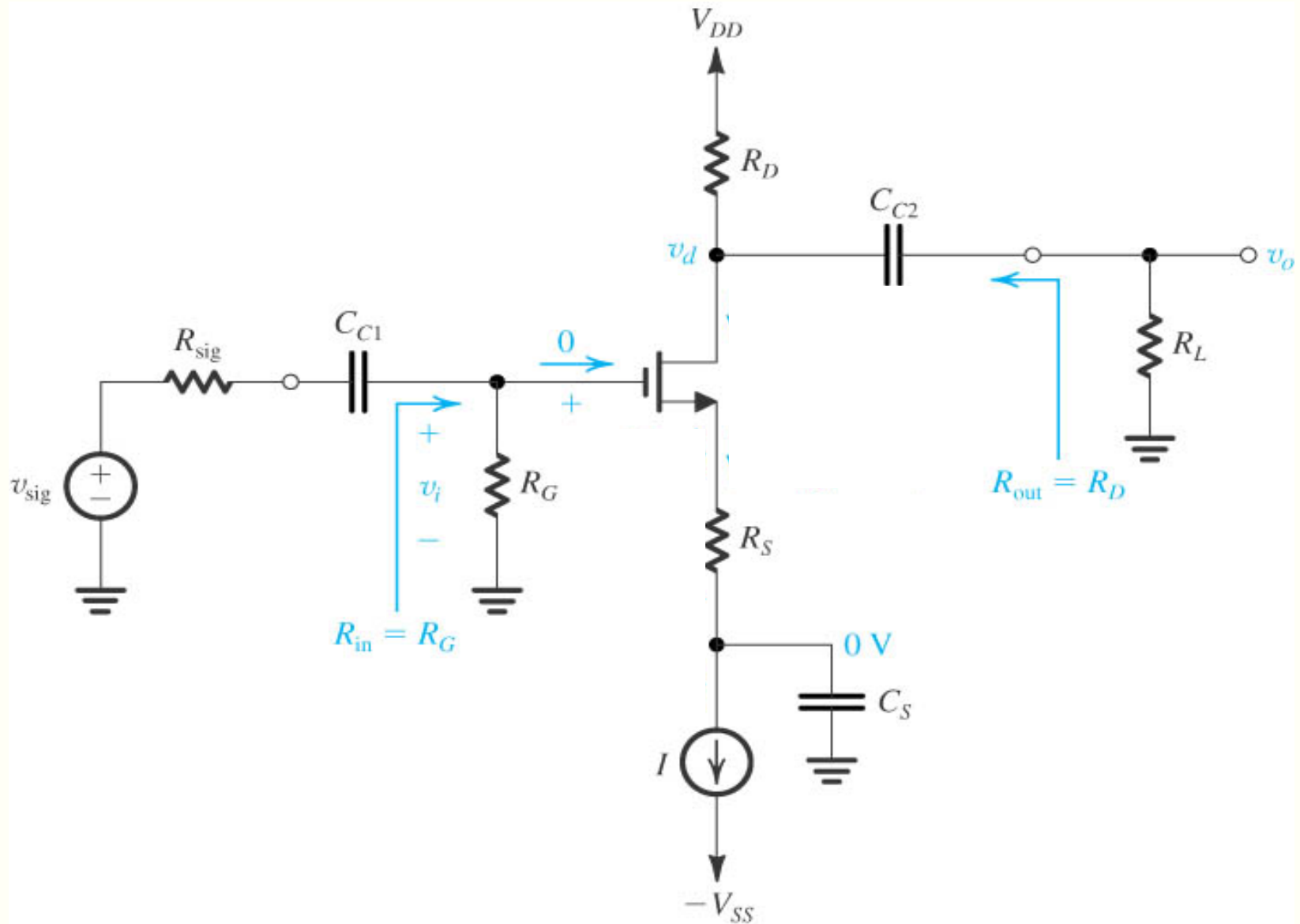
$$R_{out} = R_G \parallel r_o \parallel R_D = 8.24 \text{ k}\Omega$$

Common-Source Amplifier: Biasing with current source



- Biasing with constant-current source.
- C_{C1} And C_{C2} are coupling capacitors.
- C_S is the bypass capacitor.

The Common-Source Amplifier with a Source Resistance



(a)

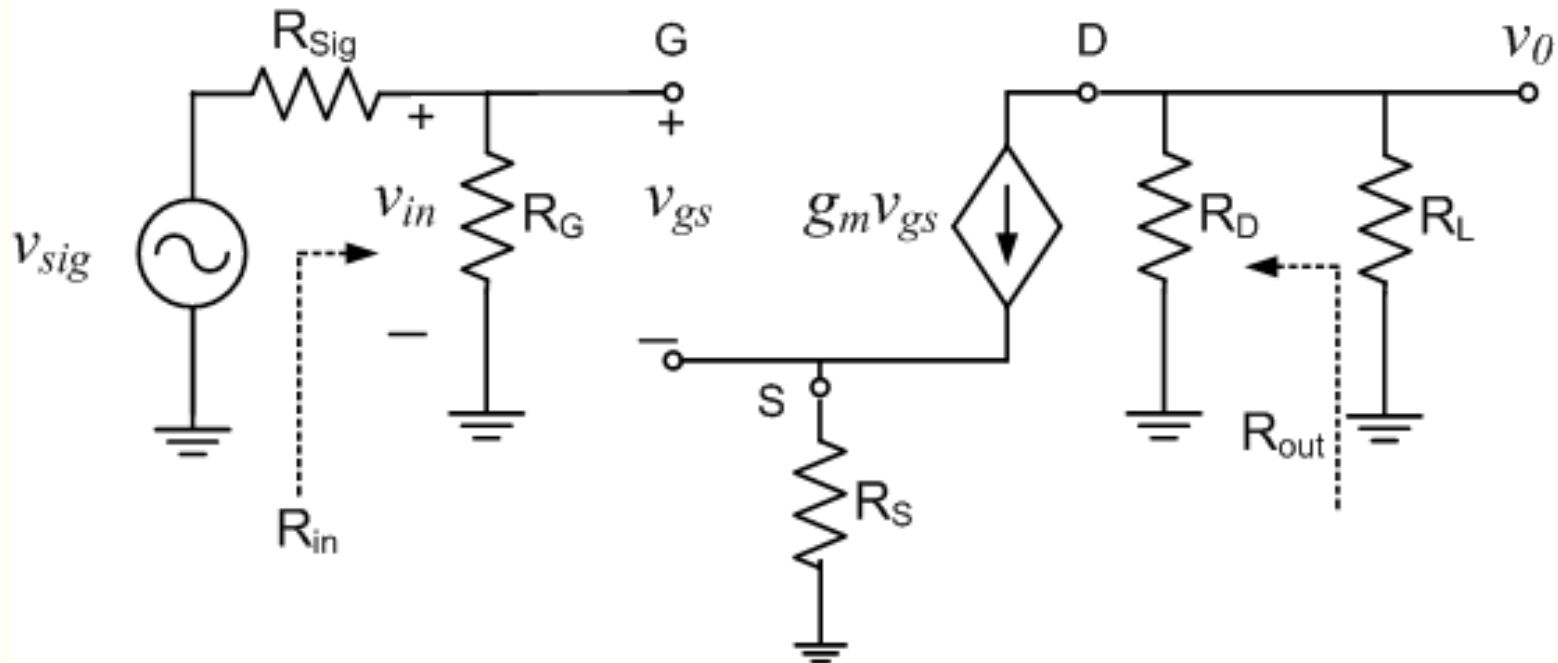
Small-signal Equivalent Circuit: Neglecting r_o

$$v_{in} = v_{gs} + g_m v_{gs} R_s$$

$$v_o = -g_m v_{gs} (R_D \parallel R_L)$$

Voltage gain

$$A_v = \frac{v_o}{v_{in}} = -\frac{g_m (R_D \parallel R_L)}{1 + g_m R_s}$$



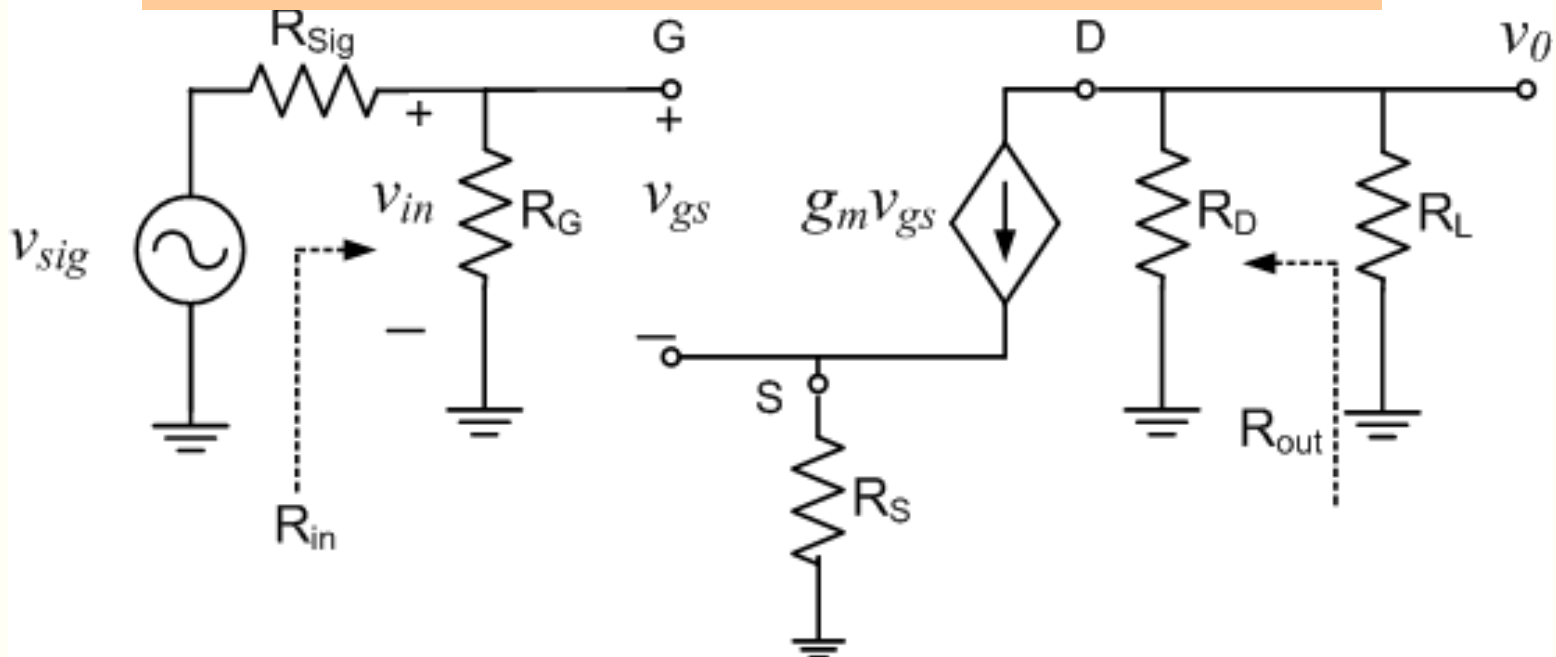
$$A_v = \frac{v_o}{v_{in}} = -\frac{g_m(R_D \parallel R_L)}{1 + g_m R_s}$$

$$v_{in} = \frac{R_G}{R_G + R_{sig}} v_{sig}$$

Overall voltage gain

$$G_v = \frac{v_o}{v_{sig}} = \frac{v_o}{v_{in}} \frac{v_{in}}{v_{sig}} = A_v \frac{v_{in}}{v_{sig}}$$

$$G_v = \frac{v_o}{v_{sig}} = -\frac{R_G}{R_G + R_{sig}} \frac{g_m(R_D \parallel R_L)}{1 + g_m R_s}$$



Characteristics of CS Amplifier with a Source Resistance

- Input resistance $R_{in} = R_G$

- Voltage gain

$$A_v = -\frac{g_m(R_D // R_L)}{1 + g_m R_S}$$

- Overall voltage gain

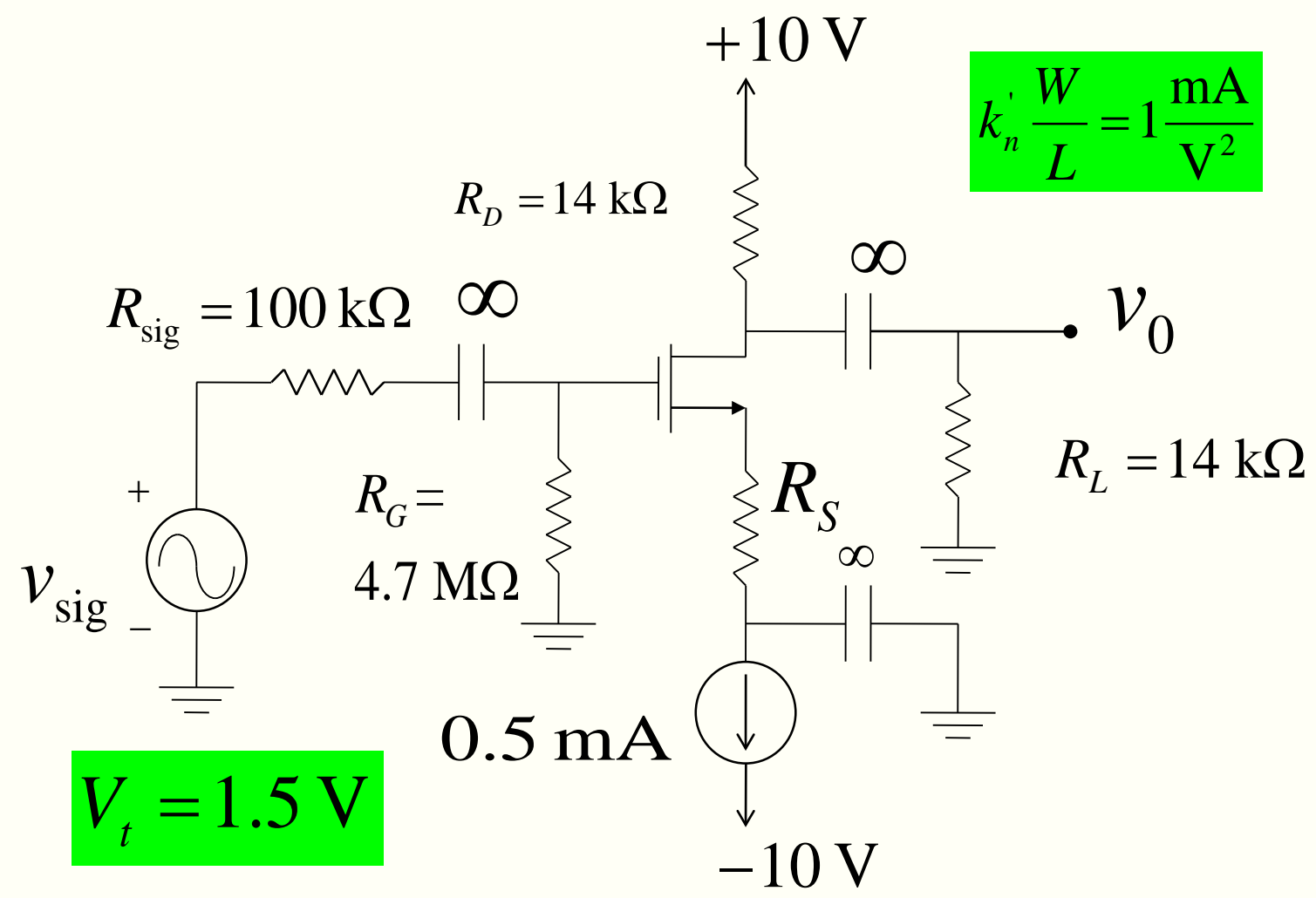
$$G_v = -\frac{R_G}{R_G + R_{sig}} \frac{g_m(R_D // R_L)}{1 + g_m R_S}$$

- Output resistance

$$R_{out} = R_D$$

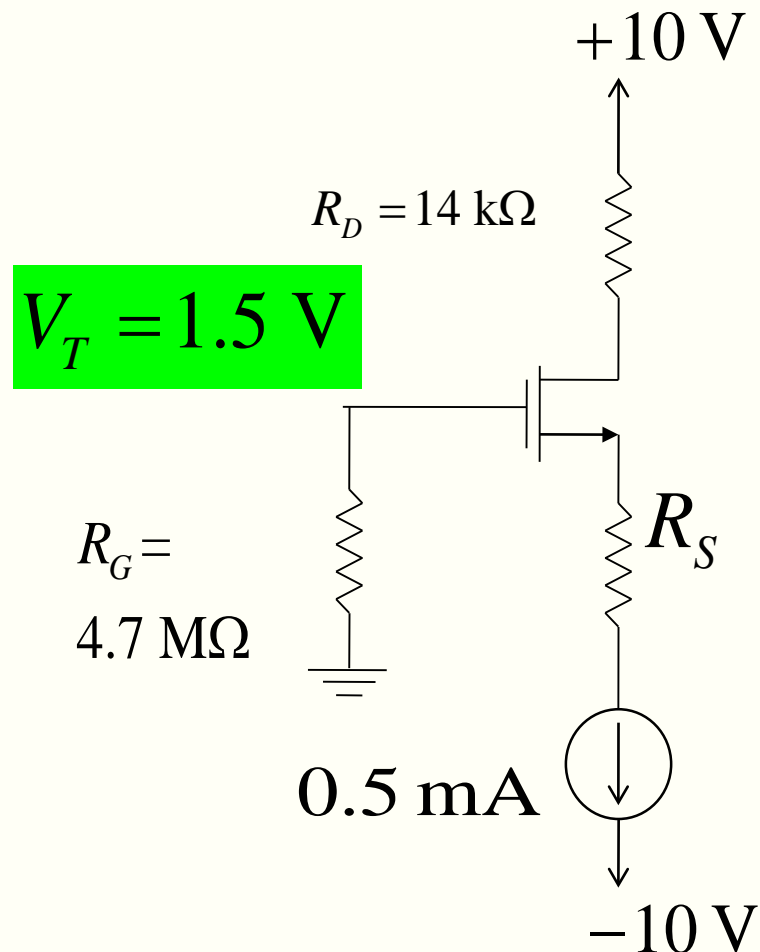
Example 9: Common Source Amplifier

Compute the small- signal voltage gain for the circuit shown in figure below with $R_s = 2\text{ k}\Omega$, $k'_n W / L = 1\text{ mA/V}^2$, and $V_t = 1.5\text{ V}$.



Example 9 (Contd.)

DC Analysis:



$$V_G = 0 \text{ and } I_D = I_S = 0.5 \text{ mA}$$

$$\begin{aligned} V_D &= 10 - R_D I_D \\ &= 10 - 14\text{k} \cdot 0.5\text{mA} = 3 \text{ V} \end{aligned}$$

$$I_D = \frac{1}{2} k'_n \frac{W}{L} (V_{GS} - V_t)^2$$

$$0.5 \text{ mA} = \frac{1}{2} 1 \times 10^{-3} (V_{GS} - 1.5)^2$$

$$\Rightarrow V_{GS} - 1.5 = \pm 1$$

$$\Rightarrow V_{GS} = 2.5 \text{ V or } 0.5 \text{ V}$$

MOSFET is in saturation mode

$$v_{GS} > V_T$$

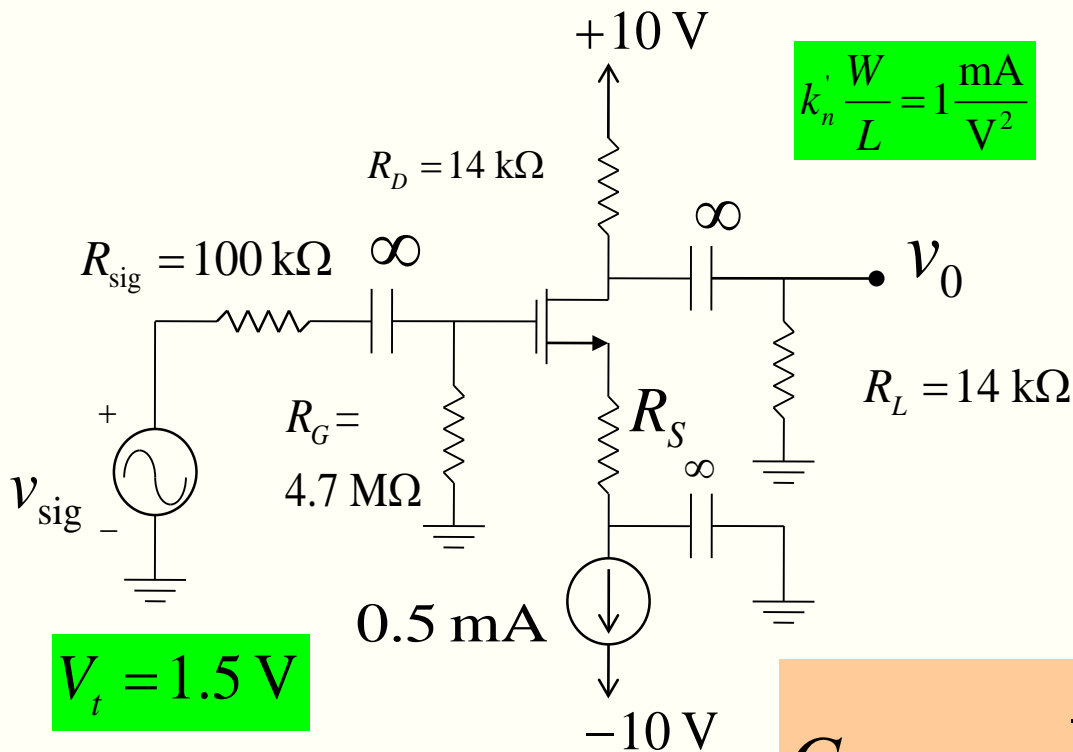
$$V_{GS} = 2.5 \text{ V}$$

For small signal analysis:

$$g_m = k'_n \frac{W}{L} (V_{GS} - V_t)$$

$$g_m = k'_n \frac{W}{L} (V_{GS} - V_t) = 10^{-3} (2.5 - 1.5) = 1 \text{ mS}$$

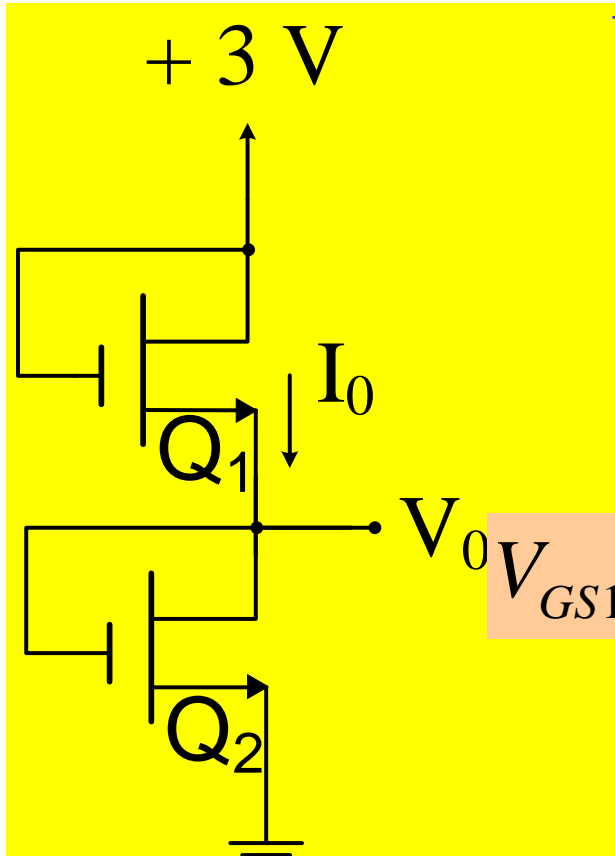
$$G_v = \frac{v_o}{v_{sig}} = - \frac{R_G}{R_G + R_{sig}} \frac{g_m (R_D \parallel R_L)}{1 + g_m R_s}$$



$$G_v = \frac{-4.7\text{M}}{4.7\text{M} + 100 \text{ k}} \frac{10^{-3} (14\text{k} \parallel 14\text{k})}{1 + 10^{-3} \times 2 \times 10^{-3}} = -2.33$$

Example: DC Analysis

For the circuit shown in Fig. below calculate the voltage V_0 and current I_0 . Both the MOSFET Q_1 and Q_2 are identical with $V_t = 1$ V, $\mu_n C_{ox} = 2.5 \mu\text{A}/\text{V}^2$, $L = 10 \mu\text{m}$, and $W = 30 \mu\text{m}$.



$V_{GD} = 0$ V for both the MOSFET.

$V_{GD} < V_t$ (MOSFET is in Saturation)

$$I_0 = I_{D1} = I_{D2}$$

$$\Rightarrow V_{GS1} = V_{GS2}$$

$$V_{GS1} + V_{GS2} = 3 \text{ V} \Rightarrow V_{GS1} = V_{GS2} = 1.5 \text{ V}$$

$$V_0 = 1.5 \text{ V}$$

$$I_D = \frac{1}{2} \mu_0 C_{ox} \frac{W}{L} (V_{GS} - V_t)^2 = \frac{1}{2} 2.5 \times 10^{-6} \cdot \frac{30}{10} (1.5 - 1)^2 = 0.9375 \mu\text{A}$$

